

Resource Summary Report

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Duke University Shared Materials Instrumentation Facility (SMIF)

RRID:SCR_027480

Type: Tool

Proper Citation

Duke University Shared Materials Instrumentation Facility (SMIF) (RRID:SCR_027480)

Resource Information

URL: <https://smif.pratt.duke.edu/>

Proper Citation: Duke University Shared Materials Instrumentation Facility (SMIF) (RRID:SCR_027480)

Description: Pratt School of Engineering core facility that enables materials, devices, and integrated systems research at Duke University in a variety of fields that include materials, devices, and integrated systems. SMIF is housed in the Fitzpatrick Center for Interdisciplinary Engineering, Medicine and Applied Sciences (FCIEMAS). The facility consists of 7,000 square feet of clean room fabrication space, and nearly 3,000 square feet of specialized laboratory space for characterization and imaging equipment.

Synonyms: Duke University Shared Materials Instrumentation Facility (SMIF)

Resource Type: access service resource, core facility, service resource

Keywords: ABRF, materials, devices, integrated systems, materials, devices, integrated systems,

Availability: Restricted

Resource Name: Duke University Shared Materials Instrumentation Facility (SMIF)

Resource ID: SCR_027480

Alternate IDs: ABRF_5158

Alternate URLs: <https://https://coremarketplace.org/?FacilityID=5158&citation=1>

Record Creation Time: 20250927T062016+0000

Record Last Update: 20260829T183514+0000

Ratings and Alerts

No rating or validation information has been found for Duke University Shared Materials Instrumentation Facility (SMIF).

No alerts have been found for Duke University Shared Materials Instrumentation Facility (SMIF).

Data and Source Information

Source: [SciCrunch Registry](#)

Usage and Citation Metrics

We found 1 mentions in open access literature.

Listed below are recent publications. The full list is available at [NIF](#) .

Ravel VM, et al. (2026) Impact of Contact Gating on Scaling of Monolayer 2D Transistors Using a Symmetric Dual-Gate Structure. ACS nano, 20(8), 7127.